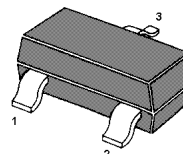


PNP Silicon Epitaxial Planar Transistor

for general purpose AF amplifier



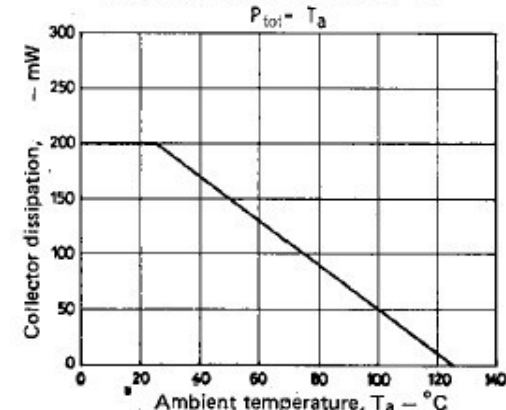
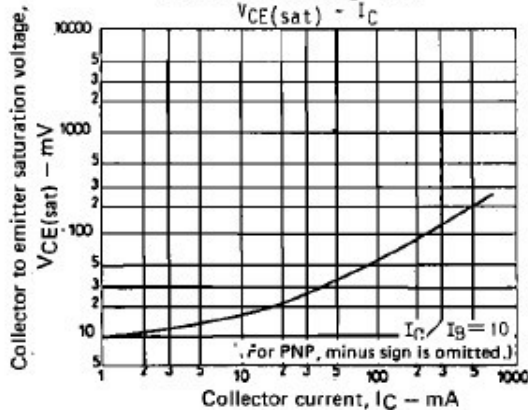
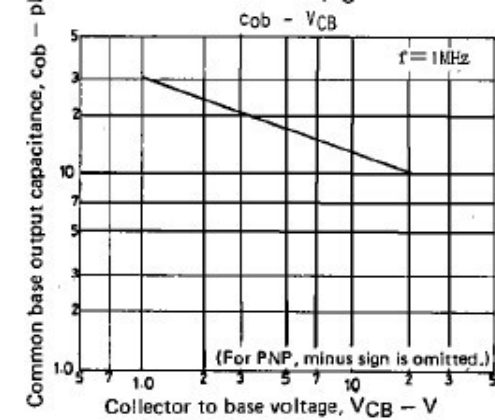
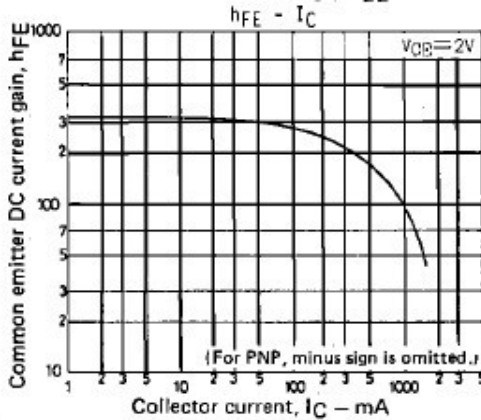
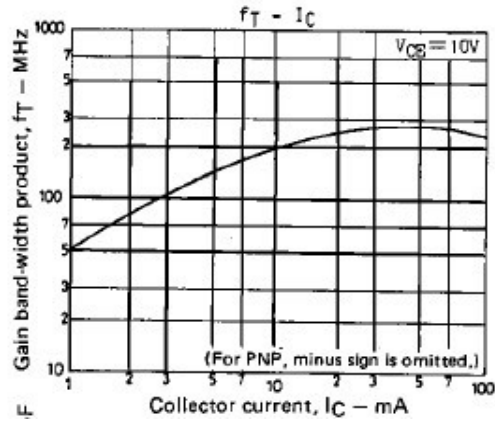
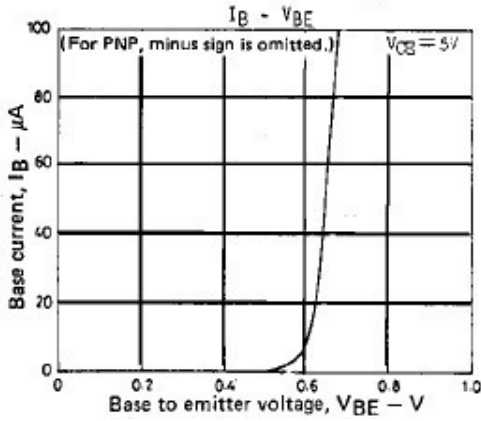
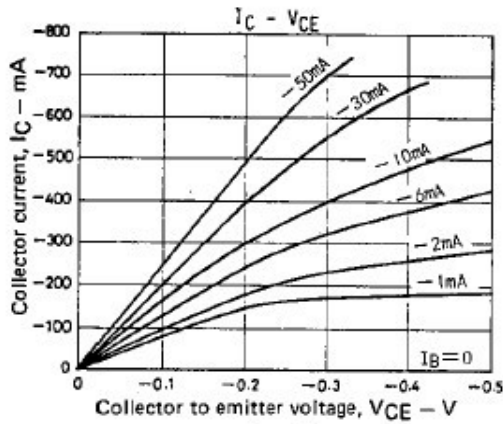
1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	20	V
Collector Emitter Voltage	$-V_{CEO}$	15	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	700	mA
Collector Current (Pulse)	$-I_{CP}$	1.5	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 50\text{ mA}$ at $-V_{CE} = 2\text{ V}$, $-I_C = 500\text{ mA}$	h_{FE} h_{FE}	200 80	- -	400 -	- -
Collector Cutoff Current at $-V_{CB} = 15\text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	20	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CEO}$	15	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 5\text{ mA}$, $-I_B = 0.5\text{ mA}$	$-V_{CE(sat)}$	-	-	35	mV
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	-	120	mV
Transition Frequency at $-V_{CE} = 10\text{ V}$, $-I_C = 50\text{ mA}$	f_T	-	250	-	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	13	-	pF

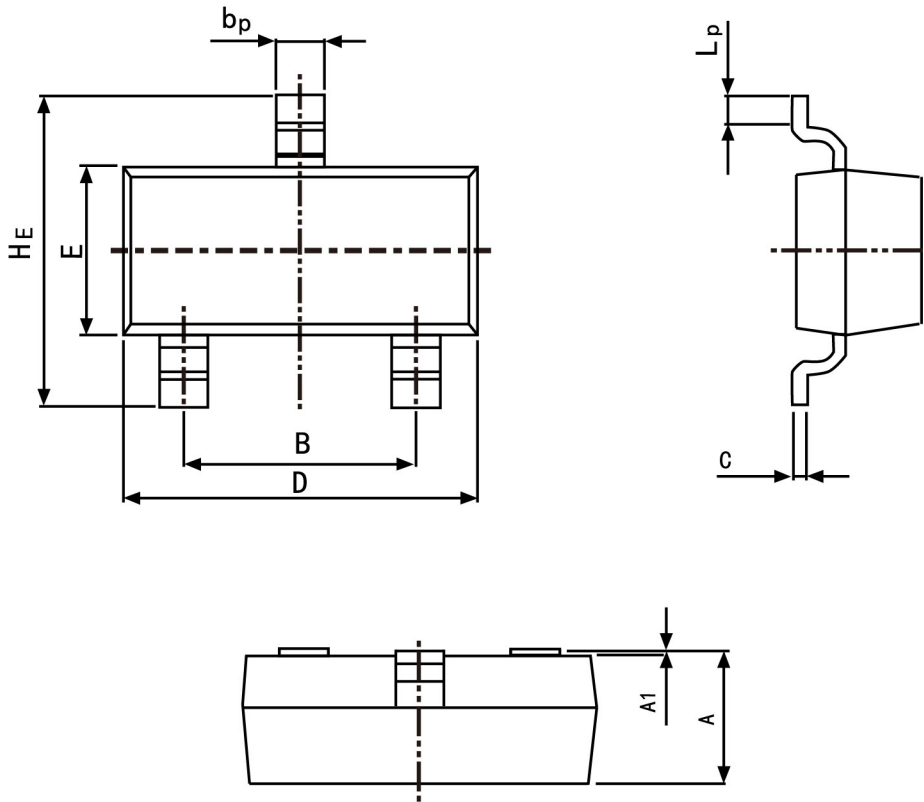




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.40
B	1.78	2.04
bp	0.35	0.50
C	0.08	0.19
D	2.70	3.10
E	1.20	1.65
HE	2.20	3.00
A1	0.100	0.013
Lp	0.20	0.50